

STPS3030/CT/CG/CR

Low drop power Schottky rectifier

Main product characteristics

I _{F(AV)}	2 x 15 A
V _{RRM}	30 V
T _j (max)	150° C
V _F (max)	0.42 V

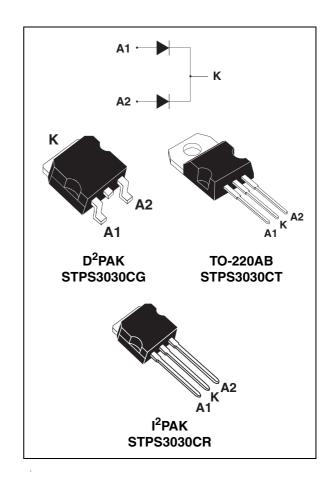
Features and benefits

- Very small conduction losses
- Negligible switching losses
- Extremely fast switching
- Low forward voltage drop for higher efficiency
- Low thermal resistance
- Avalanche capability specified

Description

Dual Schottky rectifier suited for switch mode power supply and high frequency DC to DC converters.

Packaged in TO-220AB, D²PAK and I²PAK, this device is intended for use in low voltage high frequency inverters, free-wheeling and polarity protection applications.



Rev 4

1/9

Characteristics 1

Symbol	Parameter	Value	Unit			
V _{RRM}	Repetitive peak reverse voltage			30	V	
I _{F(RMS)}	RMS forward current			30	А	
	$I_{F(AV)}$ Average forward current $T_c = 135^{\circ} C$ Per diode $\delta = 0.5$ Per device		Per diode	15	•	
^I F(AV)			Per device	30	A	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms si	nusoidal	250	А	
I _{RRM}	Peak repetitive reverse current	t _p = 2 μs squ	are F= 1 kHz	1	А	
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs s	quare	3	А	
P _{ARM}	Repetitive peak avalanche power $t_p = 1 \ \mu s \ T_j = 25^{\circ} C$			4100	W	
T _{stg}	Storage temperature range	-65 to + 150	°C			
Тj	Maximum operating junction tempera	150	°C			
dV/dt	Critical rate of rise of reverse voltage (rated V_R , $T_j = 25^{\circ}$ C)			10000	V/µs	
dPtot	1					

Table 1. Absolute ratings (limiting values, per diode)

1. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 2. Thermal resistance

Symbol	Parameter		Value	Unit
D	Junction to case TO-220AB - D ² PAK - I ² PAK	Per diode	1.2	
nth(j-c)	R _{th(j-c)} Junction to case TO-220AB - D ² PAK - I ² PAK		0.8	°C/W
R _{th(c)}	C	Coupling	0.4	

Static electrical characteristics (per diode) Table 3.

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾		T _j = 25° C	V _R = V _{RRM}		0.23	1.0	mA
IR ⁽¹⁾ Reverse leakage current	T _j = 125° C	VR − VRRM		125	180	ША	
		$T_j = 25^\circ C$	I _F = 15 A		0.44	0.49	
V _E ⁽¹⁾	V _F ⁽¹⁾ Forward voltage drop	T _j = 125° C	I _F = 15 A		0.36	0.40	v
	Torward voltage drop	$T_j = 25^\circ C$	I _F = 30 A		0.53	0.58	v
		T _j = 125° C	I _F = 30 A		0.49	0.53	

1. Pulse test: tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation: P = 0.26 x ${I_{F(AV)}}$ + 0.0107 ${I_{F}}^2_{(RMS)}$



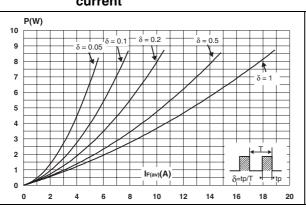
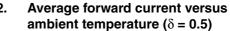


Figure 1. Conduction losses versus average Figure 2. current



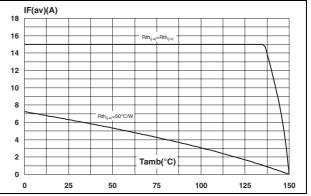


Figure 3. Normalized avalanche power derating versus pulse duration

Figure 4. Normalized avalanche power derating versus junction temperature

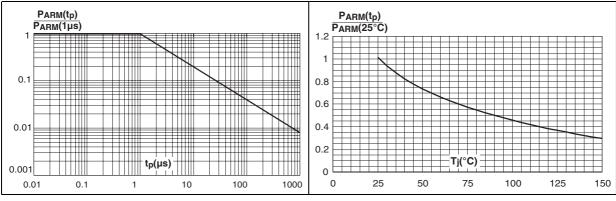
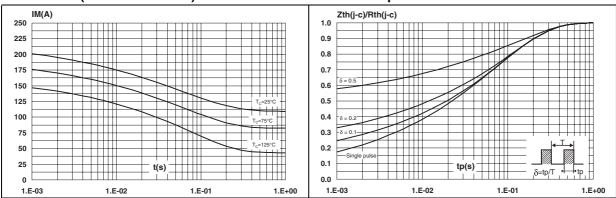


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values)

Figure 6. Relative variation of thermal impedance junction to case versus pulse duration



57

Figure 7. Reverse leakage current versus reverse voltage applied (typical values)

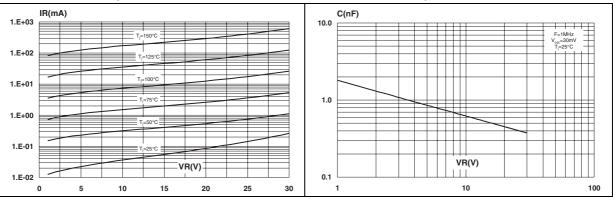
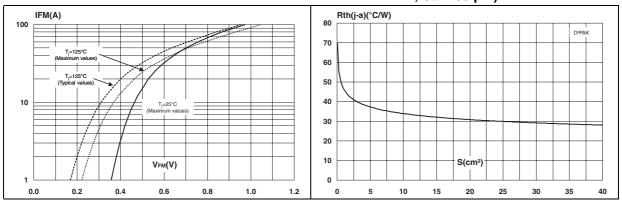


Figure 9. Forward voltage drop versus forward current

Figure 10. Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35 µm)



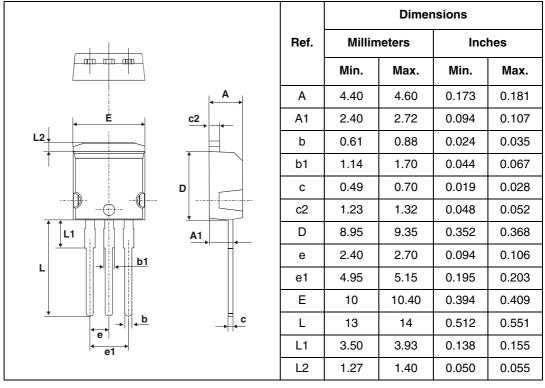
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Figure 8. Junction capacitance versus reverse voltage applied (typical values)

2 Package information

- Epoxy meets UL94,V0
- Cooling method: C
- Recommended torque value: 0.55 Nm
- Maximum torque value: 0.70 Nm

Table 4. I²PAK dimensions



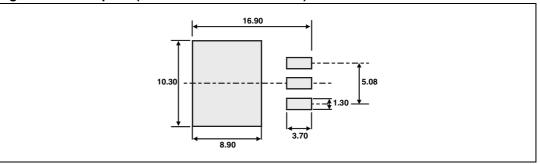


57

				Dimer	isions	
		Ref	Millimeters		Inches	
			Min.	Max.	Min.	Max.
┍┰╺┰	→⊢ A ⊣ ∢	А	4.40	4.60	0.173	0.181
	C2→– ←	A1	2.49	2.69	0.098	0.106
		A2	0.03	0.23	0.001	0.009
		В	0.70	0.93	0.027	0.037
		B2	1.14	1.70	0.045	0.067
	A1.	С	0.45	0.60	0.017	0.024
•		C2	1.23	1.36	0.048	0.054
		D	8.95	9.35	0.352	0.368
		E	10.00	10.40	0.393	0.409
		G	4.88	5.28	0.192	0.208
	T THE	L	15.00	15.85	0.590	0.624
* FLAT ZONE NO LESS THAN	M T V2	L2	1.27	1.40	0.050	0.055
	* FLAT ZONE NO LESS THAN 2mm	L3	1.40	1.75	0.055	0.069
		М	2.40	3.20	0.094	0.126
		R	0.40	typ.	0.016	6 typ.
		V2	0°	8°	0°	8°

Table 5.D²PAK dimensions

Figure 11. Footprint (dimensions in millimeters)





6/9

				Dimer	nsions	
	A	Ref	Millimeters		Inches	
			Min.	Max.	Min.	Max.
		А	4.40	4.60	0.173	0.181
		С	1.23	1.32	0.048	0.051
H2		D	2.40	2.72	0.094	0.107
Dia	→C	Е	0.49	0.70	0.019	0.027
		F	0.61	0.88	0.024	0.034
	++	F1	1.14	1.70	0.044	0.066
		F2	1.14	1.70	0.044	0.066
		G	4.95	5.15	0.194	0.202
		G1	2.40	2.70	0.094	0.106
F _▶ ↓		H2	10	10.40	0.393	0.409
G1 4		L2	16.4 typ.		0.645 typ.	
G	→ !! ← -	L4	13	14	0.511	0.551
		L5	2.65	2.95	0.104	0.116
		L6	15.25	15.75	0.600	0.620
		L7	6.20	6.60	0.244	0.259
		L9	3.50	3.93	0.137	0.154
		М	2.6	typ.	0.102	2 typ.
		Diam	3.75	3.85	0.147	0.151

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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57

57

3 Ordering information

Ordering type	Marking	Package Weight Base qt		Base qty	Delivery mode
STPS3030CT	STPS3030CT	TO-220AB	2.2 g	50	Tube
STPS3030CG	STPS3030CG	D ² PAK	1.48 g	50	Tube
STPS3030CG-TR	STPS3030CG	D ² PAK	1.48 g	1000	Tape and reel
STPS3030CR	STPS3030CR	I ² PAK	1.49 g	50	Tube

4 Revision history

Date	Revision	Changes
Jul-2006	ЗA	Initial release.
16-Oct-2006	4	Reformatted to current standards. Corrected dimensions for $\ensuremath{I}^2\ensuremath{PAK}$ in Table 4

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